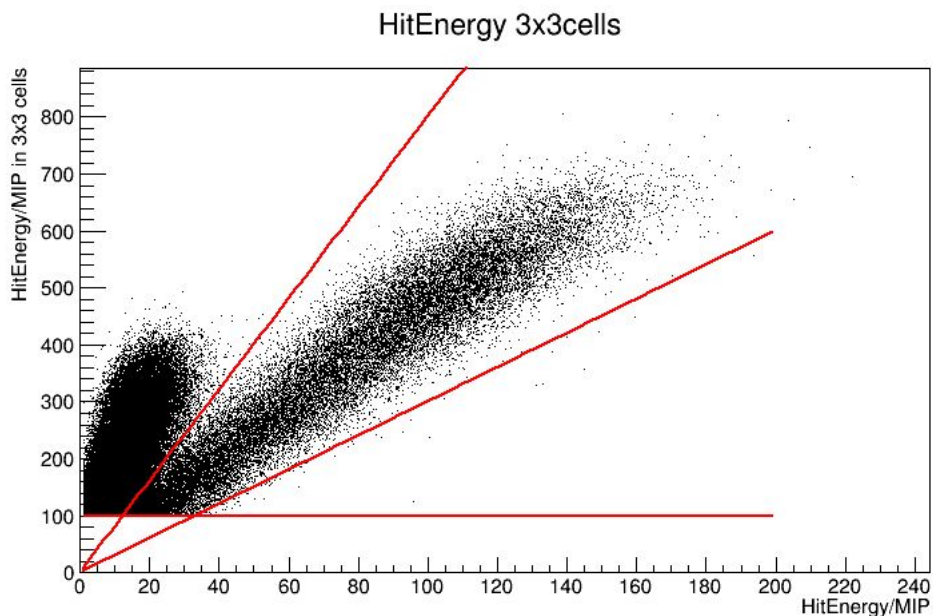
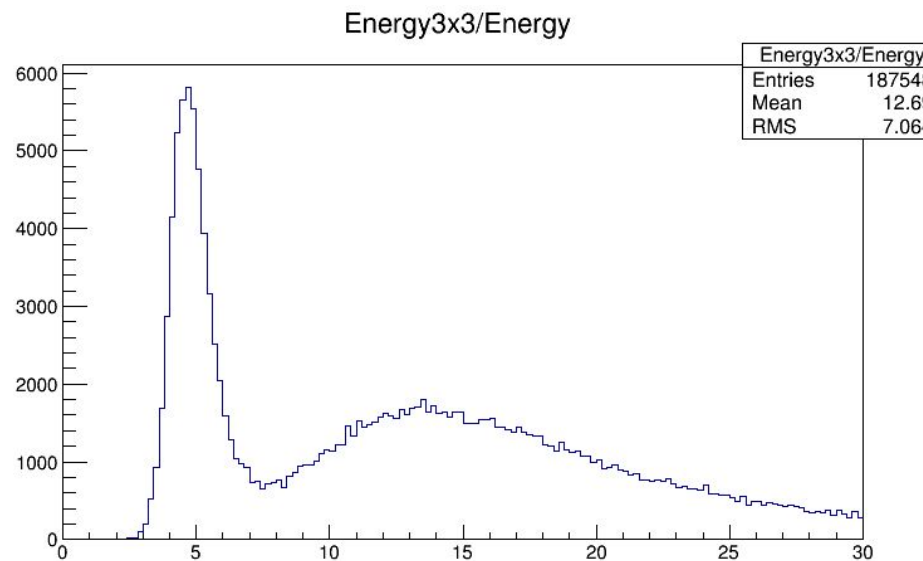


刻度研究

——击中点能量与其周围能量的关系



Hit Energy/MIP 分布

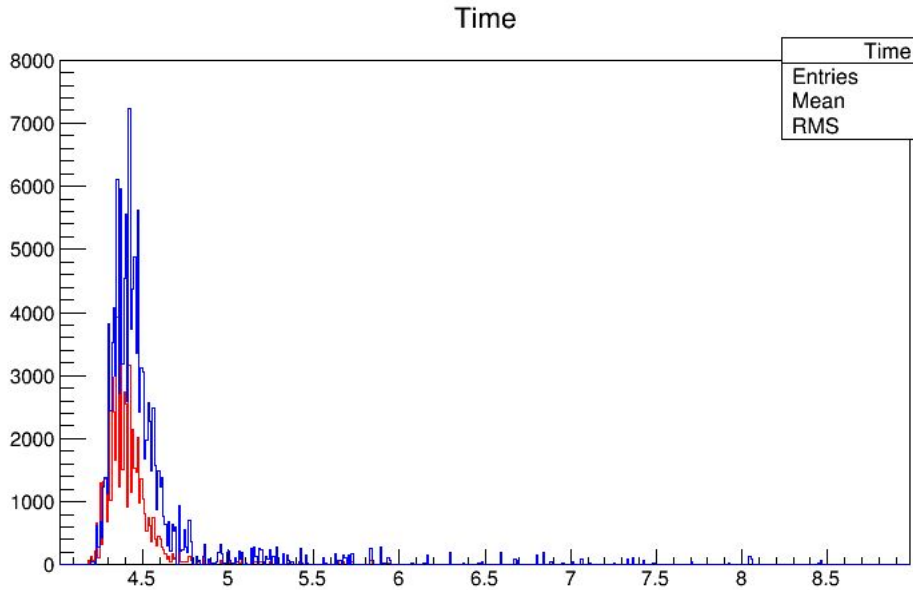


Cell Size 5x5mm

100GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 2.5x2.5mm

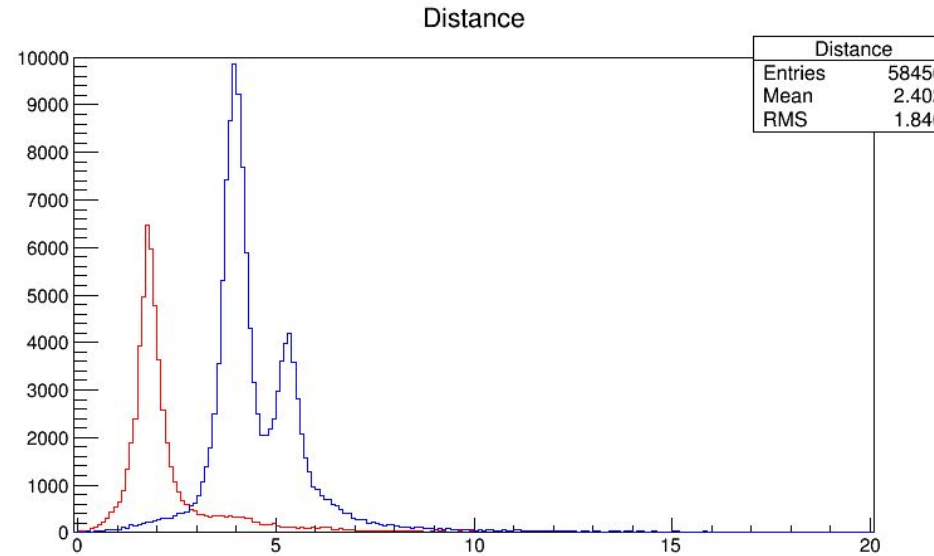
刻度研究

——击中点能量与其周围能量的关系



Hit Energy 3x3 neighbor/HitEnergy with Time

蓝色比值大于8，红色比值3~8

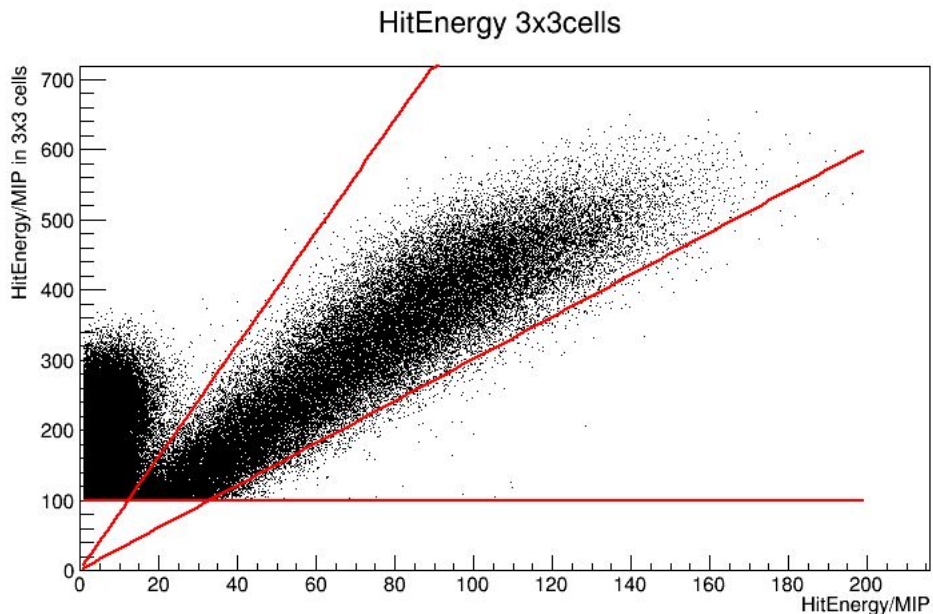


Hit Energy 3x3 neighbor/HitEnergy with Distance from Hit to Axis

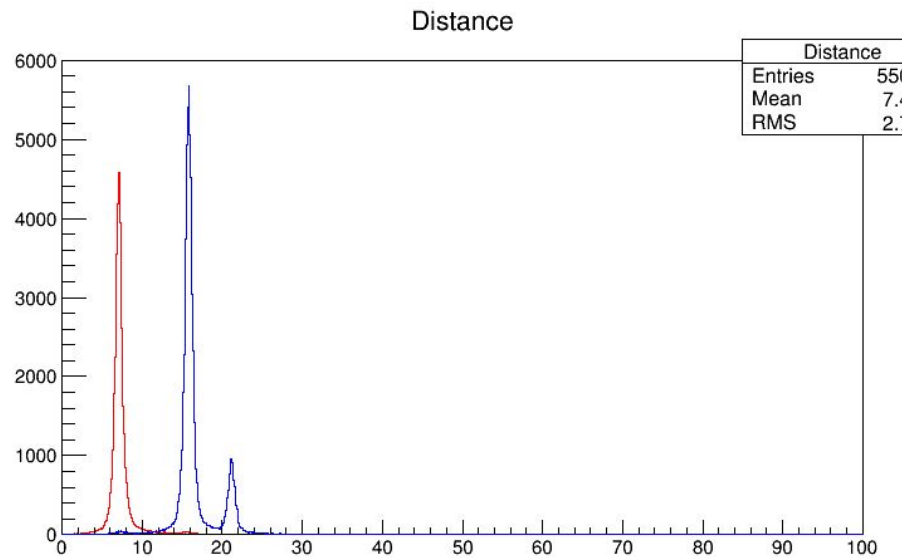
100GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 2.5x2.5mm

刻度研究

——击中点能量与其周围能量的关系



Hit Energy/MIP 分布



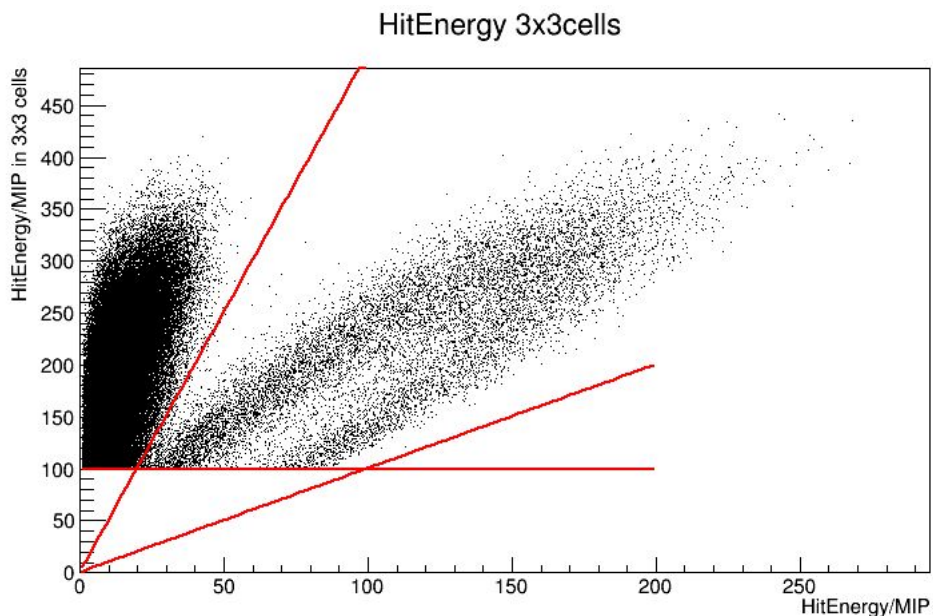
Hit Energy 3x3 neighbor/HitEnergy with Distance from Hit to Axis

蓝色比值大于8，红色比值3~8

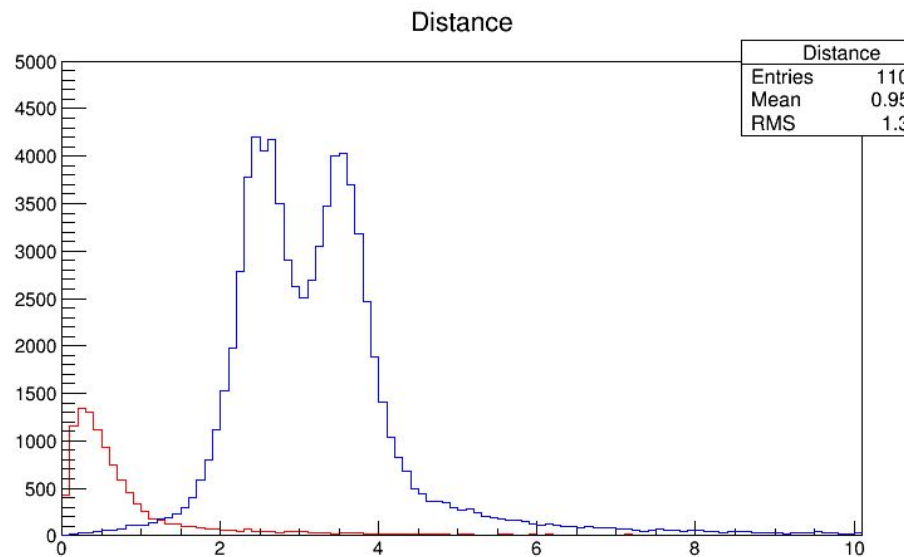
50GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 10x10mm

刻度研究

——击中点能量与其周围能量的关系



Hit Energy/MIP 分布



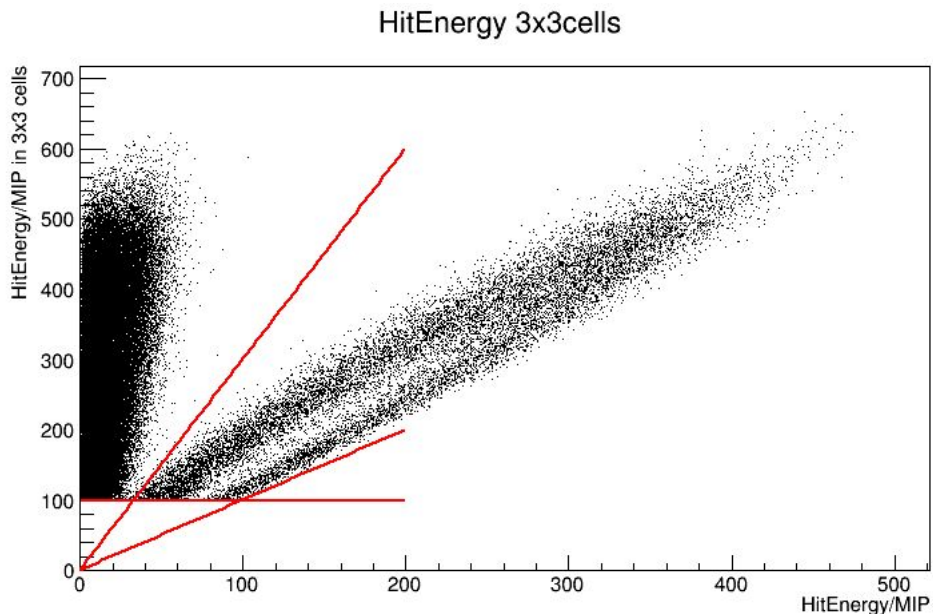
Hit Energy 3x3 neighbor/HitEnergy with Distance from Hit to Axis

蓝色比值大于5，红色比值1~5

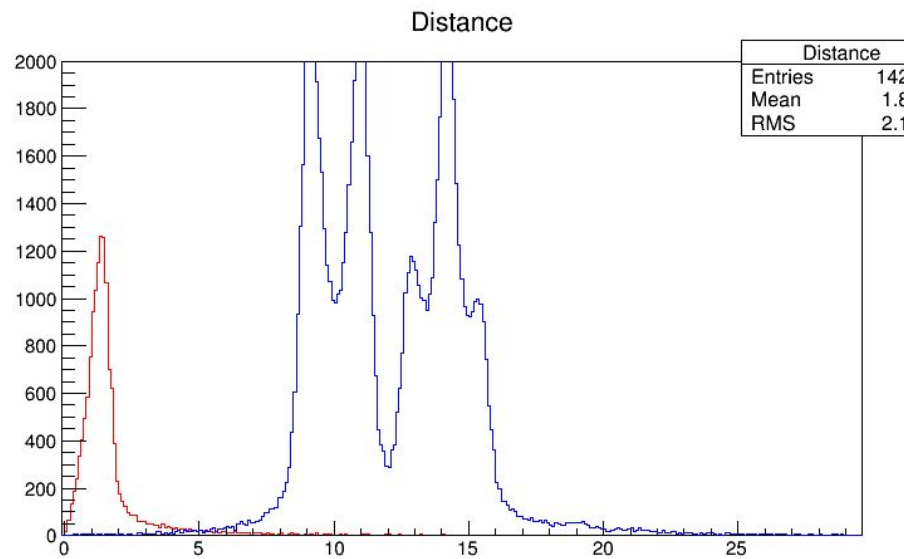
50GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 2.5x2.5mm
击中点为Cell中心

刻度研究

——击中点能量与其周围能量的关系



Hit Energy/MIP 分布



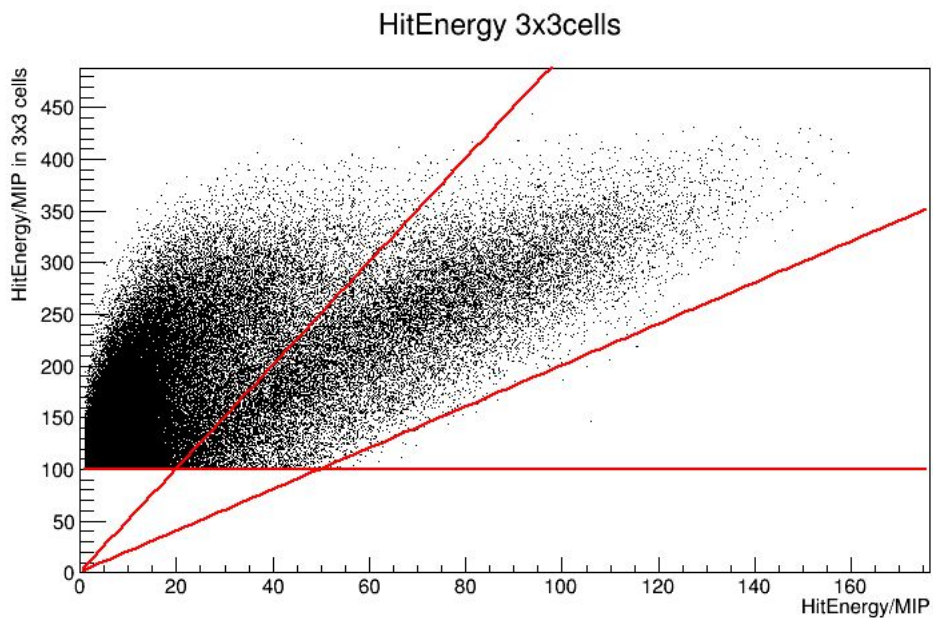
Hit Energy 3x3 neighbor/HitEnergy with Distance from Hit to Axis

蓝色比值大于3，红色比值1~3

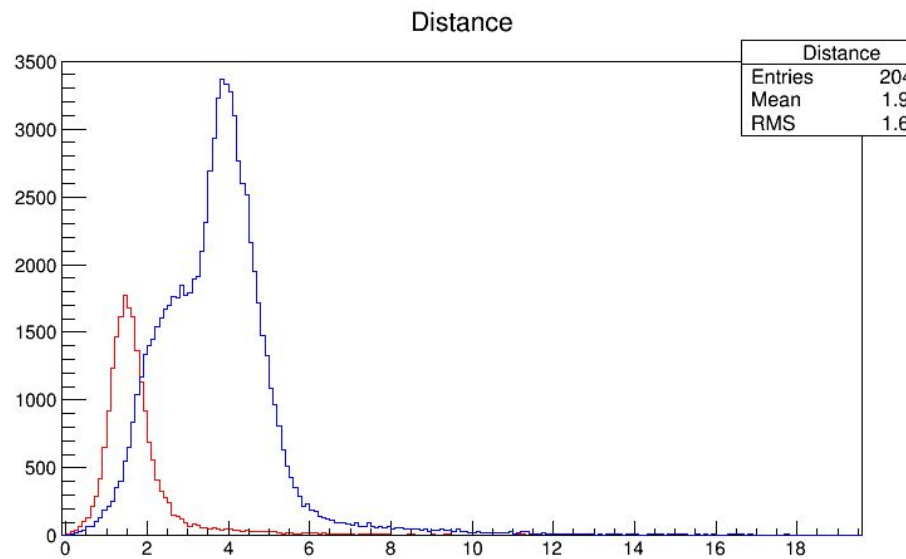
50GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 10x10mm
击中点为Cell中心

刻度研究

——击中点能量与其周围能量的关系



Hit Energy/MIP 分布



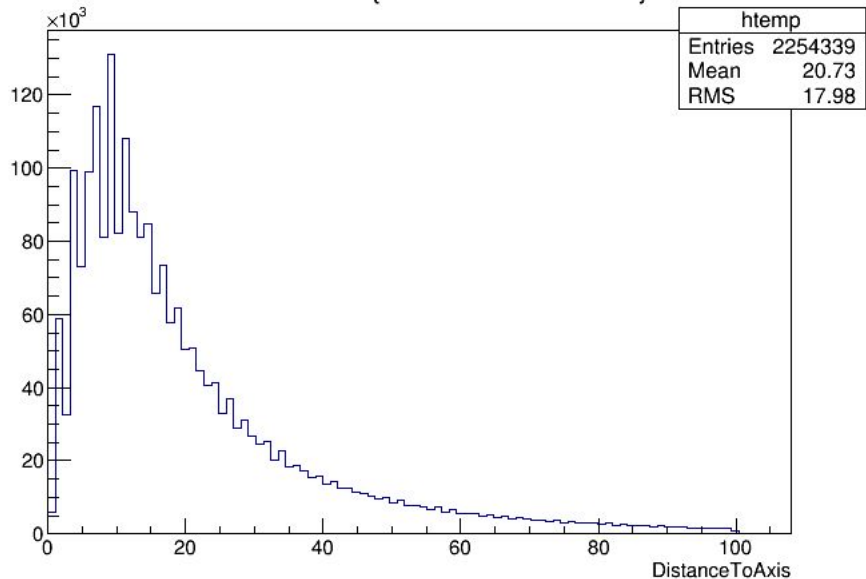
Hit Energy 3x3 neighbor/HitEnergy with Distance from Hit to Axis

蓝色比值大于7，红色比值2~7

50GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 2.5x2.5mm
倾斜约30度入射

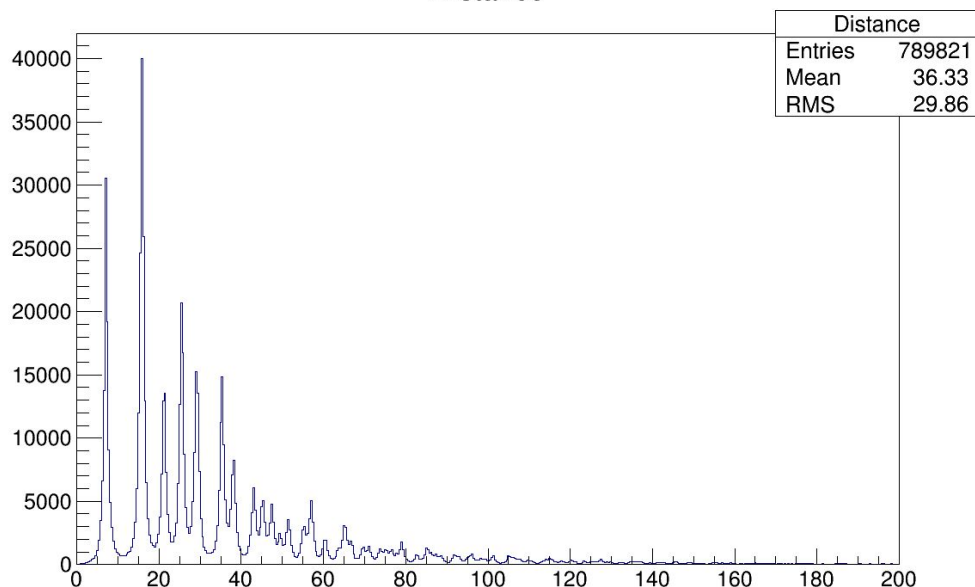
到簇射轴距离分布

DistanceToAxis {DistanceToAxis<100}



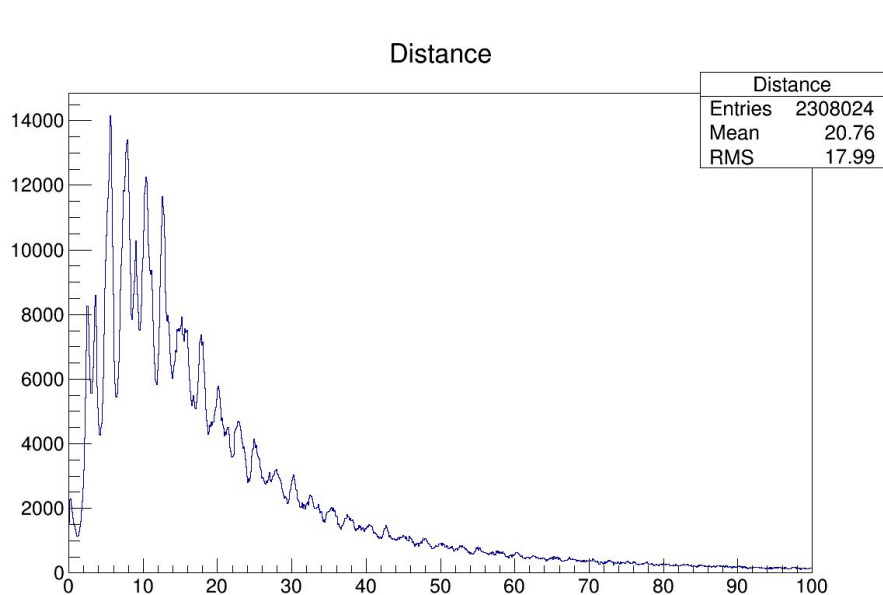
50GeVphoton
Cell Size 2.5x2.5mm

Distance



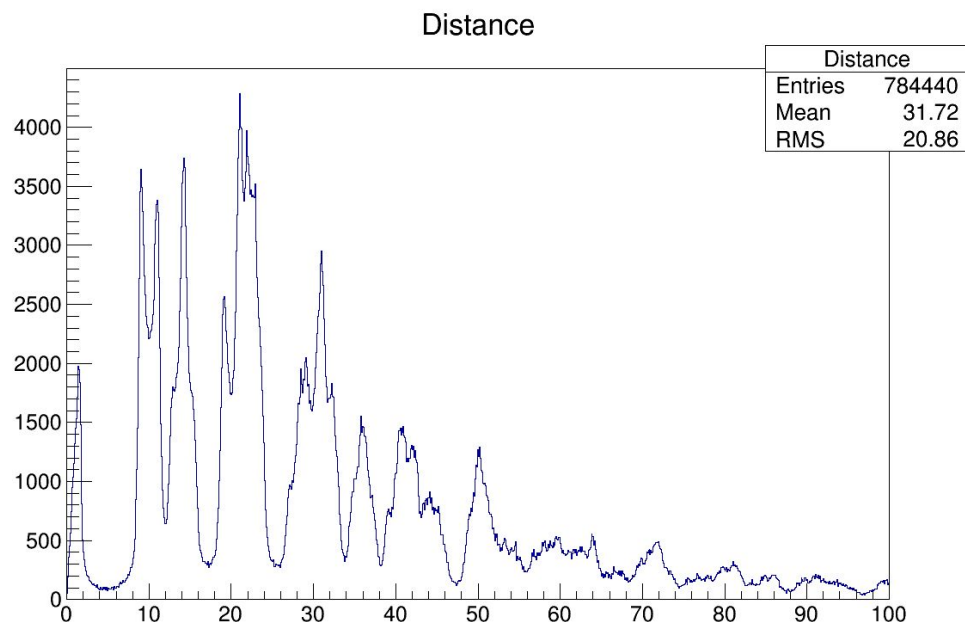
50GeVphoton
Cell Size 10x10mm

到簇射轴距离分布



50GeVphoton
Cell Size 2.5x2.5mm

入射点为Cell中心



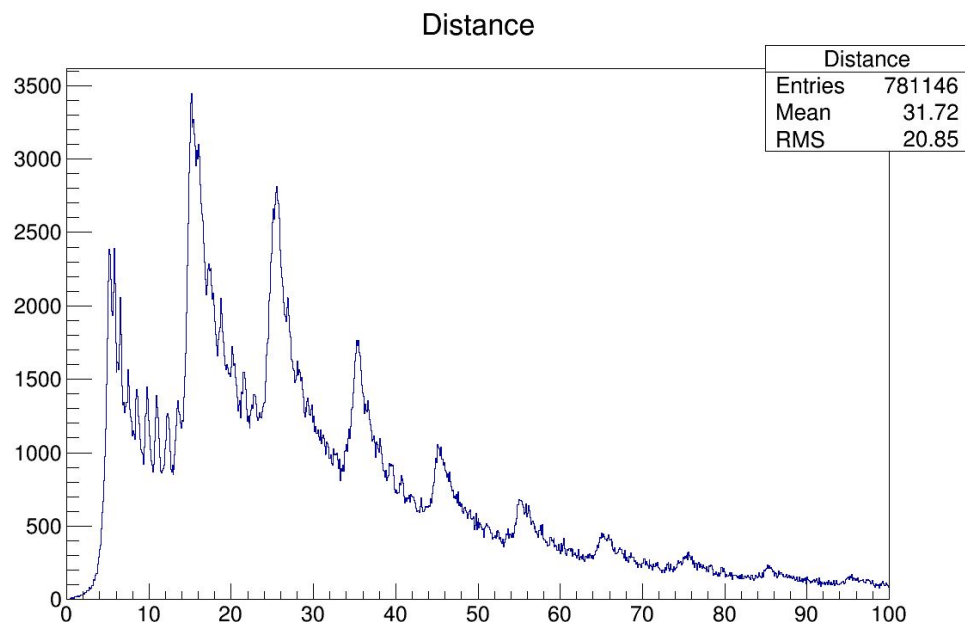
50GeVphoton
Cell Size 10x10mm

到簇射轴距离分布



50GeVphoton
Cell Size 2.5x2.5mm

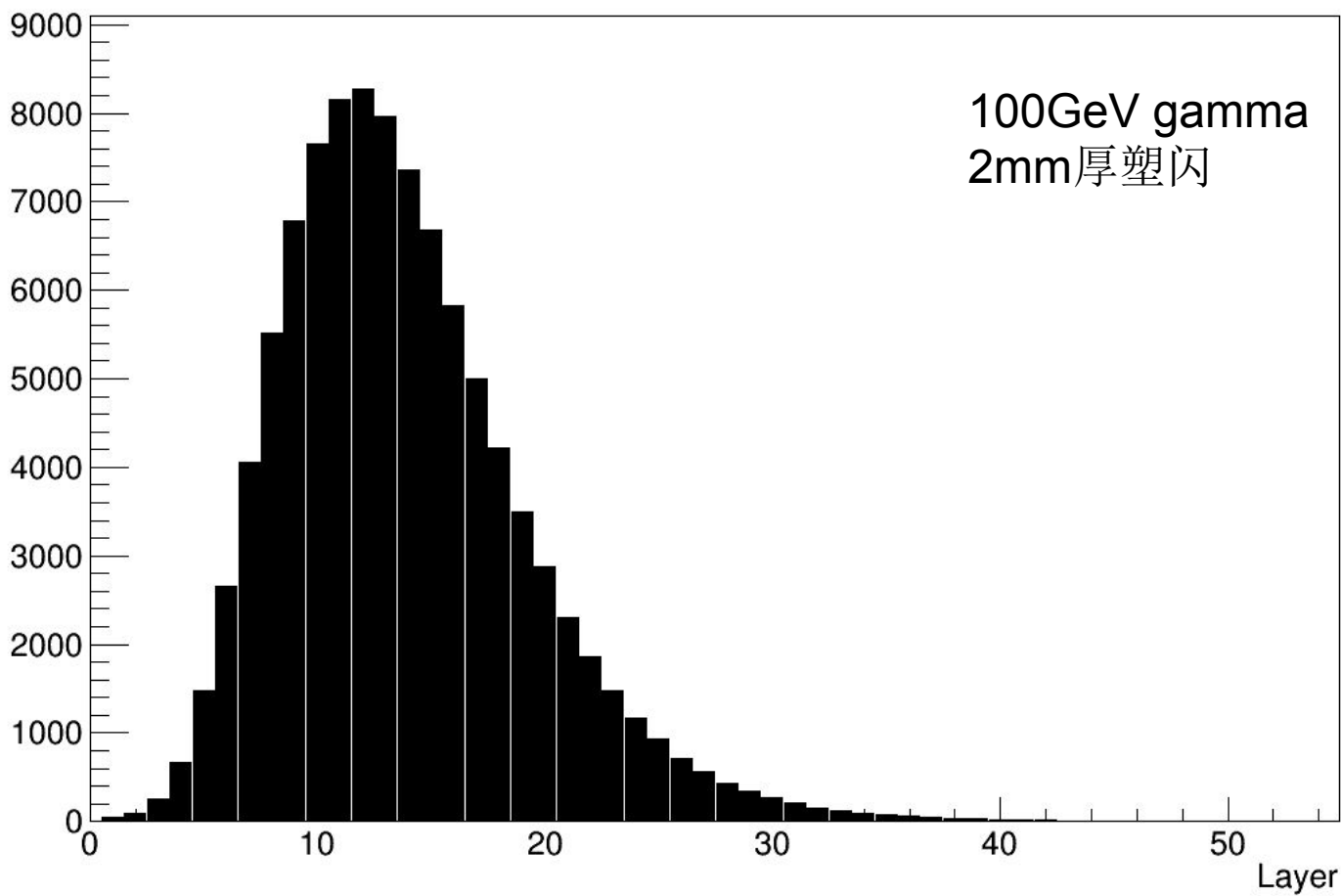
倾斜约30度入射



50GeVphoton
Cell Size 10x10mm

层数对能量泄露影响

Energy in layer



单层结构：2mm塑闪+2mmPCB+3mmW

入射粒子为gamma

